

**METHOD FOR POLYSILICON CONDUCTOR (PC) TRIMMING FOR  
SHRINKING CRITICAL DIMENSION AND ISOLATED-NESTED  
OFFSET CORRECTION**

**ABSTRACT**

5           A method of forming a semiconductor device, includes providing a  
structure having a first critical dimension, forming a lithographic pattern on the  
structure, and etching the structure with an O<sub>2</sub>-containing material to trim the first  
critical dimension to a second critical dimension, the second critical dimension  
being smaller than the first critical dimension. Thereafter, any offset between the  
10       nested features and the isolated feature can be corrected.